

### **ST8812FP**

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

#### **Features**

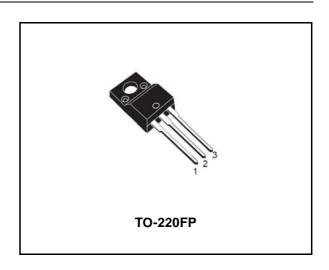
- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED
- TIGHT hfe CONTROL
- LARGE R.B.S.O.A.
- FULLY INSULATED PACKAGE U.L. COMPLIANT FOR EASY MOUNTING

### **Applications**

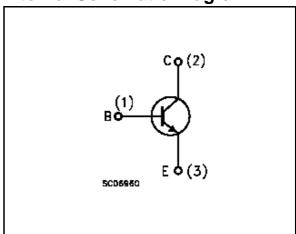
■ SWITCH MODE POWER SUPPLIES FOR CRT TV

### **Description**

The ST8812FP is manufactured using latest Multi Epitaxial Planar technology with high voltage capability. It shows wide R.B.S.O.A. and high switching speed thanks to its Cellular Emitter structure with planar edge termination and deep base diffusion.



### **Internal Schematic Diagram**



#### **Order codes**

Part Number	Marking	Package	Packing
ST8812FP	ST8812FP	TO-220FP	TUBE

1 Electrical Ratings ST8812FP

# 1 Electrical Ratings

Table 1. Absolute Maximum Rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	1150	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	600	V
V <sub>EBO</sub>	Emitte-Base Voltage (I <sub>C</sub> = 0)	15	V
I <sub>C</sub>	Collector Current	7	Α
I <sub>CM</sub>	Collector Peak Current (t <sub>P</sub> < 5ms)	12	Α
I <sub>B</sub>	Base Current	4	Α
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25°C	36	W
V <sub>isol</sub>	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	1500	V
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C
TJ	Max. Operating Junction Temperature	150	°C

Table 2. Thermal Data

Symbol	Parameter	Value	Unit
R <sub>thJ-case</sub>	Thermal Resistance Junction-Case Max	3.47	°C/W

ST8812FP 2 Electrical Characteristics

## 2 Electrical Characteristics

 $(T_{CASE} = 25^{\circ}C; unless otherwise specified)$ 

Table 3. Electrical Characteristics

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1150V V <sub>CE</sub> = 1150V	T <sub>c</sub> = 125°C			1 2	mA mA
I <sub>EBO</sub>	I <sub>EBO</sub> Emitter Cut-off Current (I <sub>C</sub> = 0)					1	mA
V <sub>CEO(sus)</sub> Note: 1	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100mA		600			V
V <sub>CE(sat)</sub> Note: 1	Collector-Emitter Saturation Voltage	$I_C = 4A$ $I_C = 4A$	$I_{B} = 0.8A$ $I_{B} = 1.2A$			3 1.5	V V
V <sub>BE(sat)</sub> Note: 1	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A	$I_{B} = 0.8A$			1.3	V
h <sub>FE</sub>	DC Current Gain	$I_{C} = 1A$ $I_{C} = 5A$ $I_{C} = 5A$	$V_{CE} = 5V$ $V_{CE} = 1V$ $V_{CE} = 5V$		25 5	9	
t <sub>s</sub>	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 4A$ $V_{Clamp} = 480V$ $I_{B1} = 0.8A$ (See <i>Figure 8</i> )	` '		1 60	1.6 120	μs ns

Note: 1 Pulsed duration = 300 µs, duty cycle ≤1.5%.

2 Electrical Characteristics ST8812FP

### 2.1 Typical characteristicsTest circuit

Figure 1. DC Current Gain

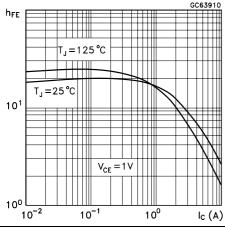


Figure 2. DC Current Gain

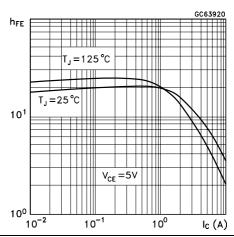
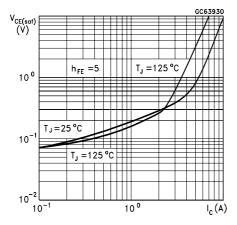


Figure 3. Collector Emitter Saturation Voltage Figure 4. Base Emitter Saturation Voltage



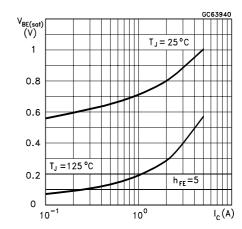
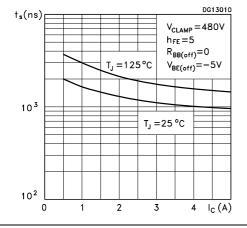
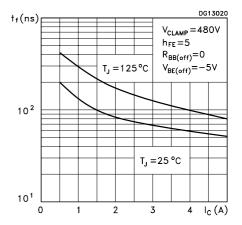


Figure 5. Inductive Load Storage Time

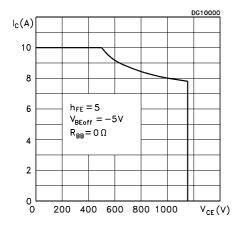
Figure 6. Inductive Load Fall Time





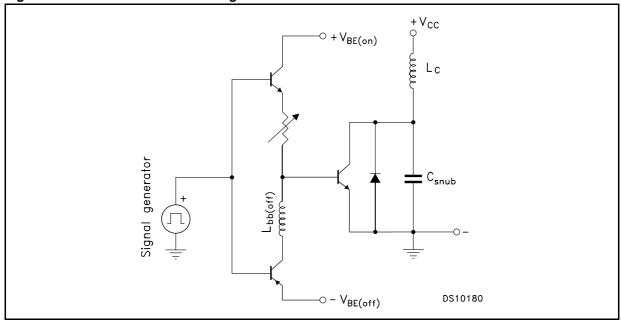
ST8812FP 2 Electrical Characteristics

Figure 7. Reverse Biased S.O.A.



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Figure 8. Inductive Load Switching Test Circuit



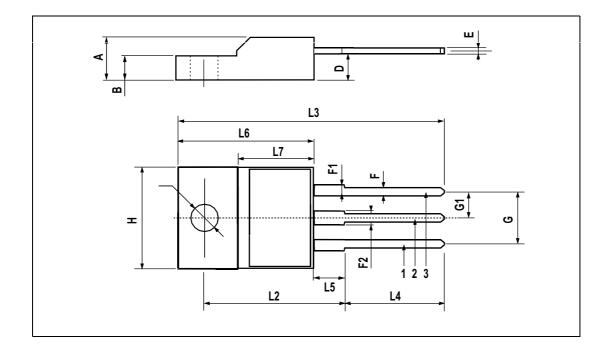
### 3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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### **TO-220FP MECHANICAL DATA**

DIM.	mm.			inch			
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	4.4		4.6	0.173		0.181	
В	2.5		2.7	0.098		0.106	
D	2.5		2.75	0.098		0.108	
Е	0.45		0.7	0.017		0.027	
F	0.75		1	0.030		0.039	
F1	1.15		1.7	0.045		0.067	
F2	1.15		1.7	0.045		0.067	
G	4.95		5.2	0.195		0.204	
G1	2.4		2.7	0.094		0.106	
Н	10		10.4	0.393		0.409	
L2		16			0.630		
L3	28.6		30.6	1.126		1.204	
L4	9.8		10.6	.0385		0.417	
L5	2.9		3.6	0.114		0.141	
L6	15.9		16.4	0.626		0.645	
L7	9		9.3	0.354		0.366	
Ø	3		3.2	0.118		0.126	



ST8812FP 4 Revision History

# 4 Revision History

Date	Revision	Changes
17-Nov-2005	1	Initial release.

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4 Revision History ST8812FP

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